

2N6676
2N6677
2N6678

**NPN SILICON
POWER TRANSISTOR**



TO-3 CASE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR 2N6676 SERIES types are NPN Silicon Power Transistors designed for high voltage switching applications.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_C=25^\circ\text{C}$)

	SYMBOL	2N6676	2N6677	2N6678	UNITS
Collector-Emitter Voltage	V_{CEV}	450	550	650	V
Collector-Emitter Voltage	V_{CEO}	300	350	400	V
Emitter-Base Voltage	V_{EBO}		8.0		V
Continuous Collector Current	I_C		15		A
Peak Collector Current	I_{CM}		20		A
Continuous Base Current	I_B		5.0		A
Power Dissipation	P_D		175		W
Operating and Storage Junction Temperature	T_J, T_{stg}		-65 to +200		$^\circ\text{C}$
Thermal Resistance	θ_{JC}		1.0		$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_C=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CEV}	$V_{CE}=\text{Rated } V_{CEV}, V_{BE(\text{off})}=1.5\text{V}$		100	μA
I_{CEV}	$V_{CE}=\text{Rated } V_{CEV}, V_{BE(\text{off})}=1.5\text{V}, T_C=100^\circ\text{C}$		1.0	mA
I_{EBO}	$V_{EB}=8.0\text{V}$		2.0	mA
BV_{CEO}	$I_C=200\text{mA}$ (2N6676)	300		V
BV_{CEO}	$I_C=200\text{mA}$ (2N6677)	350		V
BV_{CEO}	$I_C=200\text{mA}$ (2N6678)	400		V
$V_{CE(\text{SAT})}$	$I_C=15\text{A}, I_B=3.0\text{A}$		1.5	V
$V_{BE(\text{SAT})}$	$I_C=15\text{A}, I_B=3.0\text{A}$		1.5	V
h_{FE}	$V_{CE}=3.0\text{V}, I_C=15\text{A}$	8.0		
C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=1.0\text{MHz}$		500	pF
f_t	$V_{CE}=10\text{V}, I_C=1.0\text{A}, f=5.0\text{MHz}$	3.0	10	MHz
t_d	$V_{CC}=200\text{V}, I_C=15\text{A}, I_{B1}=I_{B2}=3.0\text{A}$ $t_p=20\mu\text{s}, \text{Duty Cycle}\leq 2.0\%$ $V_{BB}\approx 6.0\text{V}, R_L=13.5\Omega$		0.1	μs
t_r			0.6	μs
t_s			2.5	μs
t_f			0.5	μs

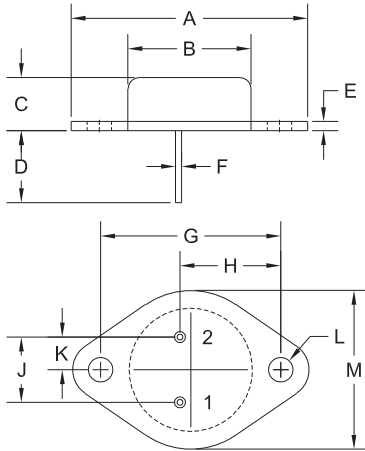
R0 (26-July 2010)

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TO-3 CASE - MECHANICAL OUTLINE



DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.516	1.573	38.50	39.96
B (DIA)	0.748	0.875	19.00	22.23
C	0.250	0.450	6.35	11.43
D	0.433	0.516	11.00	13.10
E	0.054	0.065	1.38	1.65
F	0.035	0.045	0.90	1.15
G	1.177	1.197	29.90	30.40
H	0.650	0.681	16.50	17.30
J	0.420	0.440	10.67	11.18
K	0.205	0.225	5.21	5.72
L (DIA)	0.151	0.172	3.84	4.36
M	0.984	1.050	25.00	26.67

TO-3 (REV: R2)

R2

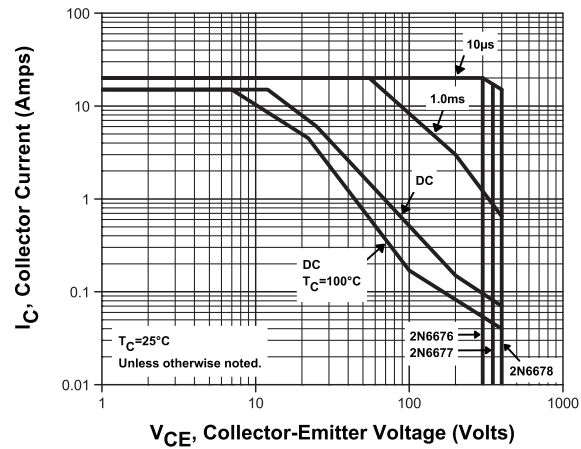
LEAD CODE:

- 1) Base
- 2) Emitter
- Case) Collector

MARKING:

FULL PART NUMBER

Safe Operating Area



R0 (26-July 2010)

OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

REQUESTING PRODUCT PLATING

1. If requesting Tin/Lead plated devices, add the suffix " TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
2. If requesting Lead (Pb) Free plated devices, add the suffix " PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

CONTACT US

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